WEJ®

MMBT5401LT1 TRANSISTOR (PNP)

SOT-23 Plastic-Encapsulate Transistors

Features

- **Power dissipation**

  P_{CM} : 0.3 W (Tamb=25°C)

- **Collector current**

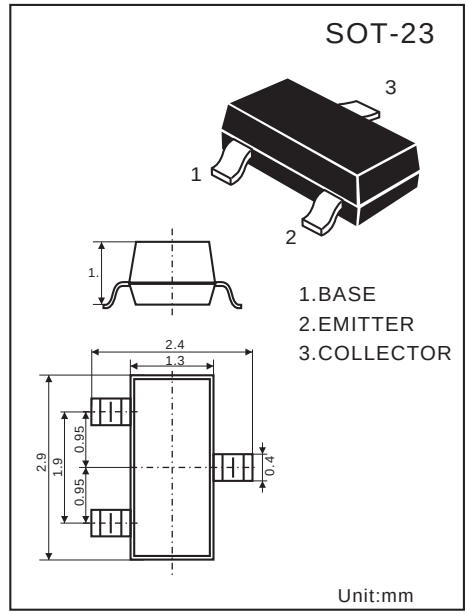
  I_{CM} : -0.6A

- **Collector-base Voltage**

  $V_{(BR)CBO}$:-160V

- **Operating and storage junction temperature range**

  T_j, T_{stg} : -55°C to +150°C



Electrical Characteristics

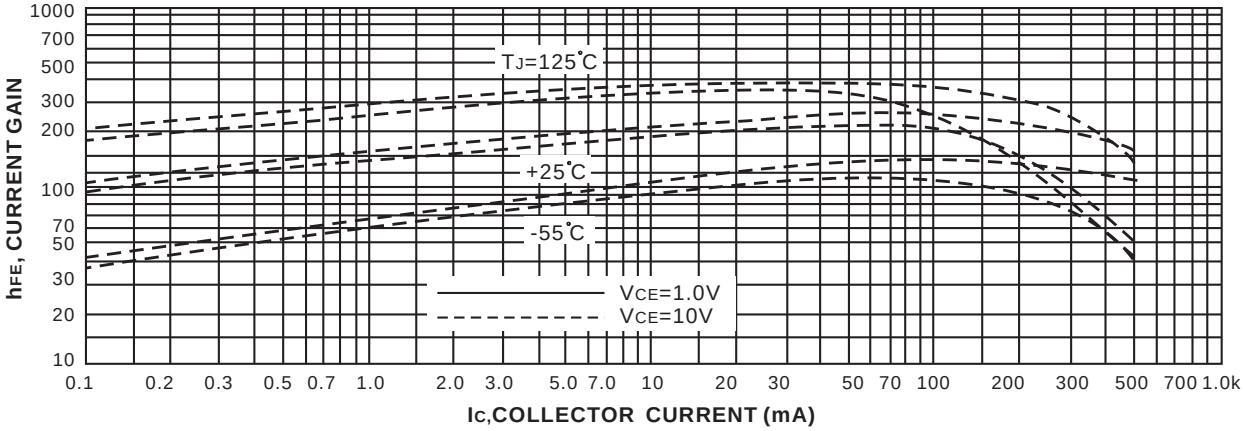
(Tamp=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-160			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1 mA, I_B=0	-150			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-10μA, I_B=0	-5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-120V, I_E=0			-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-4V, I_C=0mA			-0.1	μA
DC Current Gain	$H_{FE(1)}$	V_{CE}=-5V, I_C=-1mA	80			
	$H_{FE(2)}$	V_{CE}=-5V, I_C=-10mA	100		200	
	$H_{FE(3)}$	V_{CE}=-5V, I_C=-50mA	50			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=-50mA			-1	V
Transition Frequency	f_T	V_{CE}=-20V, I_C=-50mA ,f=100MHz	100			MHz

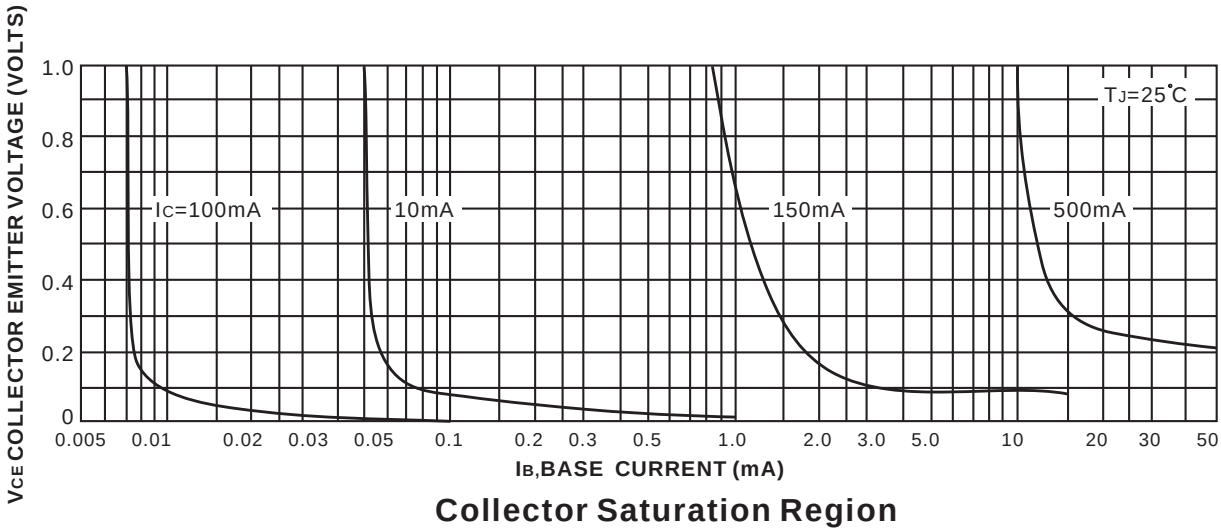
Device Marking

MMBT5401LT1 = 2L

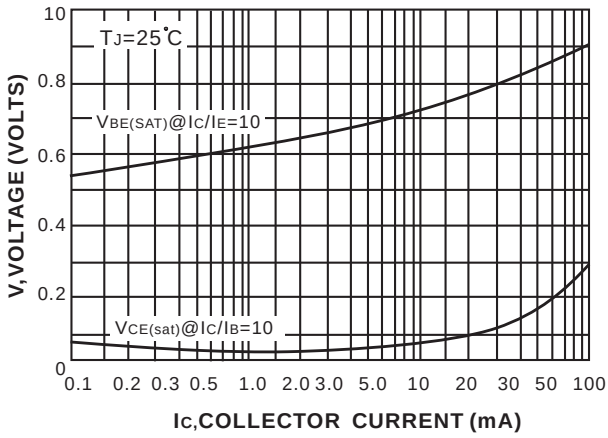
Typical Characteristics



DC Current Gain



Collector Saturation Region



"On" Voltages